

Power Management Switch ICs for PCs and Digital Consumer Products



1ch Small Package High Side Switch ICs for USB Devices and Memory Cards

BD2246G, BD2247G

No. xxxxxxxxxx

Description

BD2246G and BD2247G are low on-resistance N-channel MOSFET high-side power switches, optimized for Universal Serial Bus (USB) applications. BD2246G and BD2247G are equipped with the function of over-current detection, thermal shutdown, under-voltage lockout and soft-start.

Features

- 1) Low On-Resistance (Typ. 110mΩ) N-channel MOSFET Built-in
- 2) Reverse Current Protection when Power Switch Off
- 3) Output Discharge Function
- 4) Over-Current Detection
- 5) Thermal Shutdown
- 6) Open-Drain Fault Flag Output
- 7) Under-Voltage Lockout
- 8) Soft-Start Circuit
- 9) Input Voltage Range: 2.7V ~ 5.5V
- 10) Control Input Logic Active-High (BD2246G), Active-Low (BD2247G)
- 11) SSOP5 Package

Absolute Maximum Ratings (Ta=25 °C)

Parameter	Symbol	Ratings	Unit
VIN supply voltage	VIN	-0.3 ~ 6.0	V
EN(/EN) input voltage	VEN(/EN)	-0.3 ~ 6.0	V
/OC voltage	V/OC	-0.3 ~ 6.0	V
/OC sink current	I/OC	5	mA
VOUT voltage	VOUT	-0.3 ~ 6.0	V
Storage temperature	TSTG	-55 ~ 150	
Power dissipation	Pd	675 ^{*1}	mW

^{*1} Mounted on 70mm x 70mm x 1.6mm glass epoxy board. Reduce 5.4mW per 1 °C above 25 °C

* This IC is not designed to be radiation-proof.

Operating Conditions

Parameter	Symbol	Ratings			Unit
		Min.	Typ.	Max.	
VIN operating voltage	VIN	2.7	5.0	5.5	V
Operating temperature	TOPR	-40	-	85	

Electrical Characteristics ($V_{IN} = 5V$, $T_a = 25$, unless otherwise specified.)

BD2246G

DC Characteristics

Parameter	Symbol	Limits			Unit	Conditions
		Min.	Typ.	Max.		
Operating current	I _{DD}	-	110	160	μA	$V_{EN} = 5V$, $V_{OUT} = \text{open}$, $V_{IN} = 5V$
		-	75	110		$V_{EN} = 3.3V$, $V_{OUT} = \text{open}$, $V_{IN} = 3.3V$
Standby current	I _{STB}	-	0.01	5	μA	$V_{EN} = 0V$, $V_{OUT} = \text{open}$, $V_{IN} = 5V$
EN input voltage	V _{ENH}	2.0	-	-	V	High input, $V_{IN} = 3.3\sim 5V$
	V _{ENL}	-	-	0.8	V	Low input, $V_{IN} = 5V$
		-	-	0.6		Low input, $V_{IN} = 3.3V$
EN input leakage	I _{EN}	-1	0.01	1	μA	$V_{EN} = 0V$ or $5V$
On-resistance	R _{ON}	-	110	155	mΩ	$I_{OUT} = 500mA$, $V_{IN} = 5V$
		-	130	180		$I_{OUT} = 500mA$, $V_{IN} = 3.3V$
Reverse leak current	I _{REV}	-	-	1	μA	$V_{OUT} = 5V$, $V_{IN} = 0V$
Over-current threshold	I _{TH}	630	765	900	mA	$V_{IN} = 5V$
		600	740	890		$V_{IN} = 3.3V$
Short circuit output current	I _{SC}	350	500	650	mA	$V_{OUT} = 0V, \text{RMS}$, $V_{IN} = 3.3\sim 5V$
Output discharge resistance	R _{DISC}	30	60	120	Ω	$I_{DISC} = 1mA$, $V_{IN} = 5V$
		50	100	200		$I_{DISC} = 1mA$, $V_{IN} = 3.3V$
/OC output low voltage	V _{/OC}	-	-	0.4	V	$I_{/OC} = 0.5mA$, $V_{IN} = 3.3\sim 5V$
UVLO threshold	V _{TUVH}	2.1	2.3	2.5	V	V_{IN} increasing
	V _{TUVL}	2.0	2.2	2.4	V	V_{IN} decreasing

AC Characteristics

Parameter	Symbol	Limits			Unit	Conditions
		Min.	Typ.	Max.		
Output rise time	T _{ON1}	-	1	6	ms	$R_L = 20\Omega$, $V_{IN} = 3.3\sim 5V$
Output turn-on time	T _{ON2}	-	1.5	10	ms	$R_L = 20\Omega$, $V_{IN} = 3.3\sim 5V$
Output fall time	T _{OFF1}	-	1	20	μs	$R_L = 20\Omega$, $V_{IN} = 3.3\sim 5V$
Output turn-off time	T _{OFF2}	-	3	40	μs	$R_L = 20\Omega$, $V_{IN} = 3.3\sim 5V$
/OC delay time	T _{/OC}	10	15	20	ms	$V_{IN} = 5V$
		11	16	21		$V_{IN} = 3.3V$

BD2247G

DC Characteristics

Parameter	Symbol	Limits			Unit	Conditions
		Min.	Typ.	Max.		
Operating current	I _{DD}	-	110	160	μA	V _{EN} = 0V, V _{OUT} = open, V _{IN} = 5V
		-	75	110		V _{EN} = 0V, V _{OUT} = open, V _{IN} = 3.3V
Standby current	I _{STB}	-	0.01	5	μA	V _{EN} = 5V, V _{OUT} = open, V _{IN} = 5V
/EN input voltage	V _{ENH}	2.0	-	-	V	High input, V _{IN} = 3.3~5V
	V _{ENL}	-	-	0.8	V	Low input, V _{IN} = 5V
		-	-	0.6		Low input, V _{IN} = 3.3V
/EN input leakage	I _{EN}	-1	0.01	1	μA	V _{EN} = 0V or 5V
On-resistance	R _{ON}	-	110	155	mΩ	I _{OUT} = 500mA, V _{IN} = 5V
		-	130	180		I _{OUT} = 500mA, V _{IN} = 3.3V
Reverse leak current	I _{REV}	-	-	1	μA	V _{OUT} = 5V, V _{IN} = 0V
Over-current threshold	I _{TH}	630	765	900	mA	V _{IN} = 5V
		600	740	890		V _{IN} = 3.3V
Short circuit output current	I _{SC}	350	500	650	mA	V _{OUT} = 0V, RMS, V _{IN} = 3.3~5V
Output discharge resistance	R _{DISC}	30	60	120	Ω	I _{DISC} = 1mA, V _{IN} = 5V
		50	100	200		I _{DISC} = 1mA, V _{IN} = 3.3V
/OC output low voltage	V _{OC}	-	-	0.4	V	I _{OC} = 0.5mA, V _{IN} = 3.3~5V
UVLO threshold	V _{TUVH}	2.1	2.3	2.5	V	V _{IN} increasing
	V _{TUVL}	2.0	2.2	2.4	V	V _{IN} decreasing

AC Characteristics

Parameter	Symbol	Limits			Unit	Conditions
		Min.	Typ.	Max.		
Output rise time	T _{ON1}	-	1	6	ms	R _L = 20Ω, V _{IN} = 3.3~5V
Output turn-on time	T _{ON2}	-	1.5	10	ms	R _L = 20Ω, V _{IN} = 3.3~5V
Output fall time	T _{OFF1}	-	1	20	μs	R _L = 20Ω, V _{IN} = 3.3~5V
Output turn-off time	T _{OFF2}	-	3	40	μs	R _L = 20Ω, V _{IN} = 3.3~5V
/OC delay time	T _{OC}	10	15	20	ms	V _{IN} = 5V
		11	16	21		V _{IN} = 3.3V

Measurement Circuit

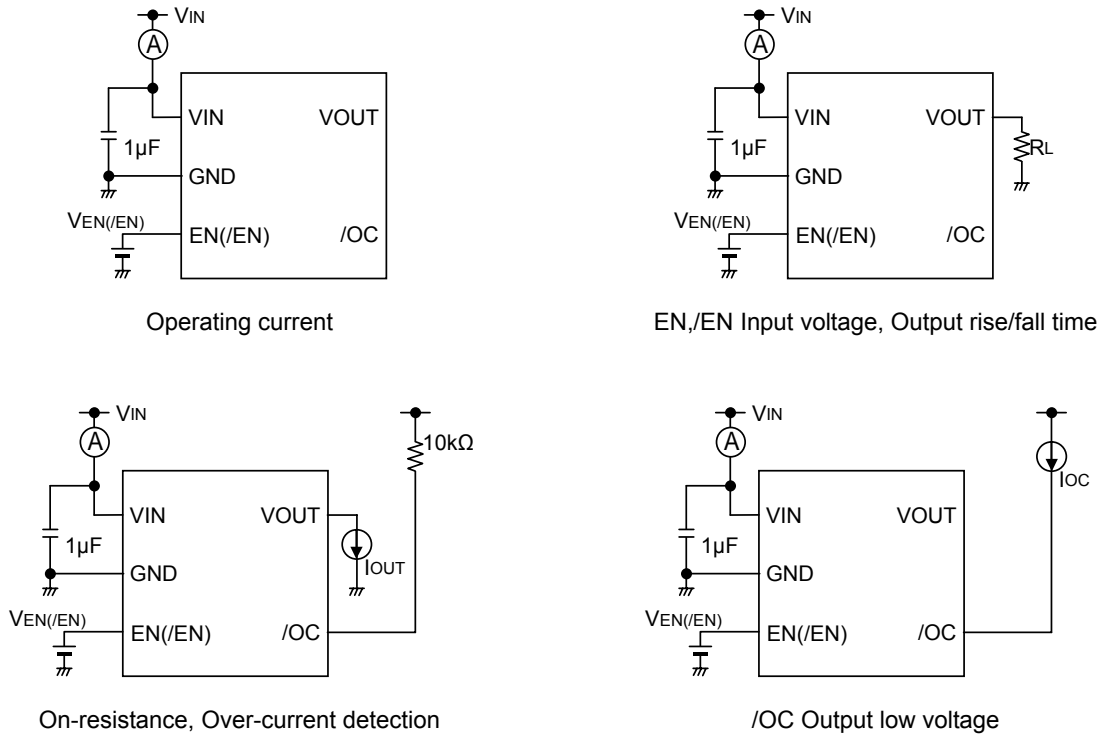


Fig.1 Measurement circuit

Timing Diagram

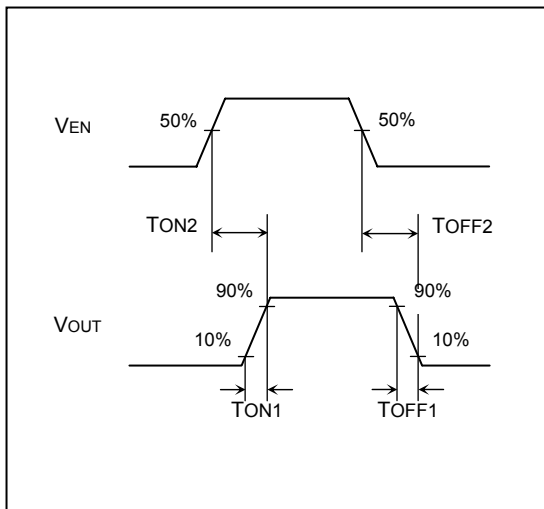


Fig.2 Output rise/fall time (BD2246G)

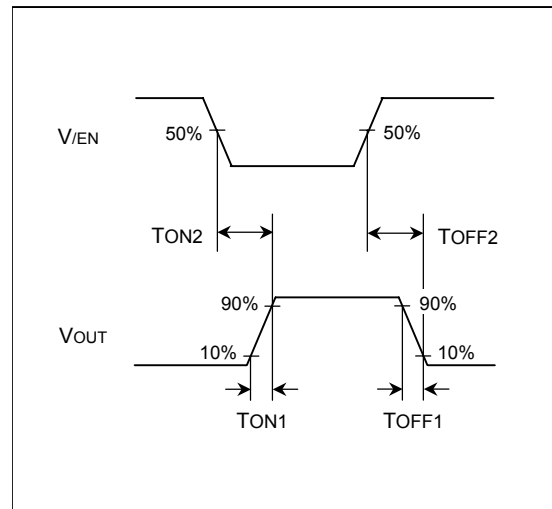


Fig.3 Output rise/fall time (BD2247G)

Reference Data

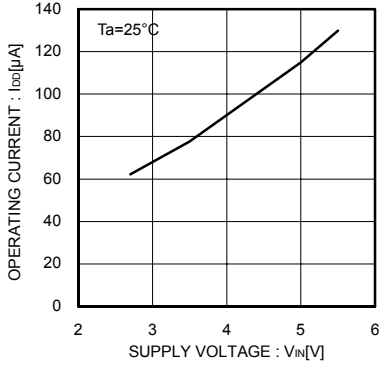


Fig.4 Operating current EN,/EN enable

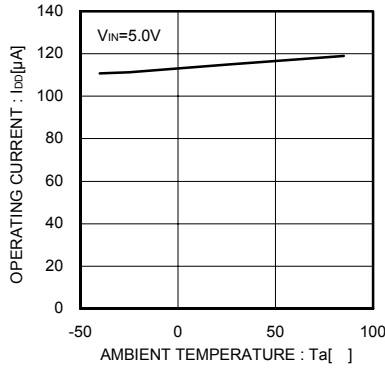


Fig.5 Operating current EN,/EN enable

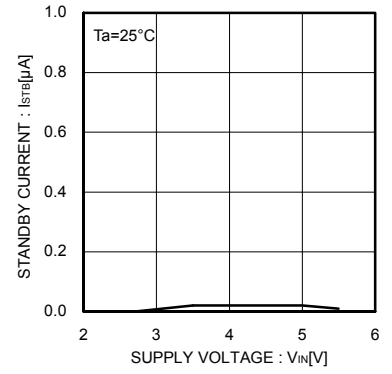


Fig.6 Standby current EN,/EN disable

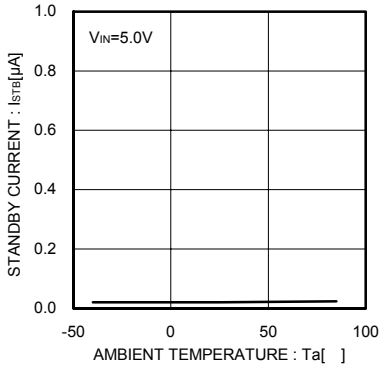


Fig.7 Standby current EN,/EN disable

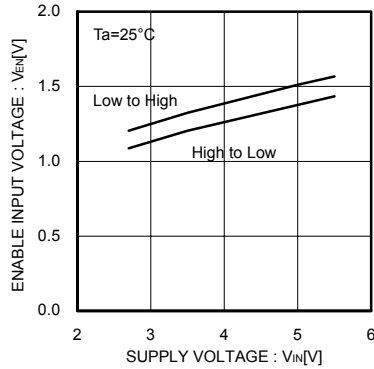


Fig.8 EN,/EN input voltage

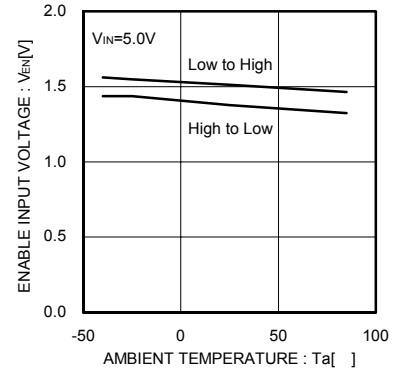


Fig.9 EN,/EN input voltage

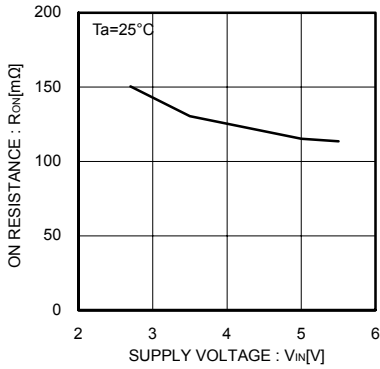


Fig.10 On-resistance

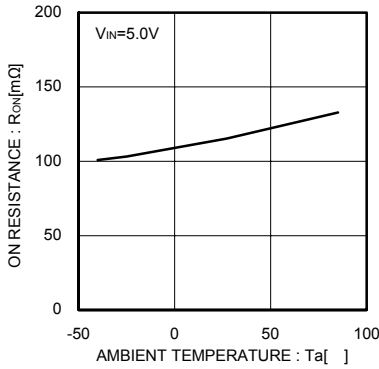


Fig.11 On-resistance

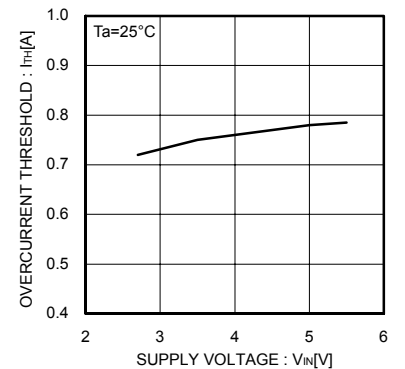


Fig.12 Over-current threshold

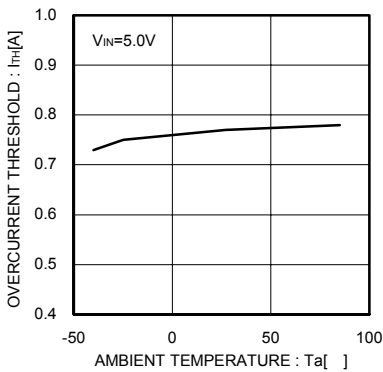


Fig.13 Over-current threshold

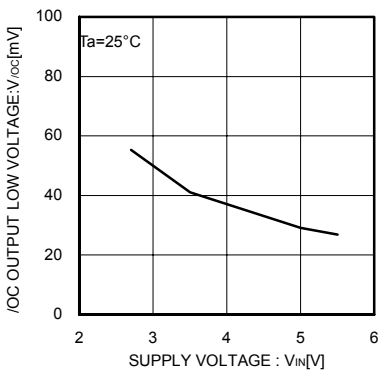


Fig.14 /OC output low voltage

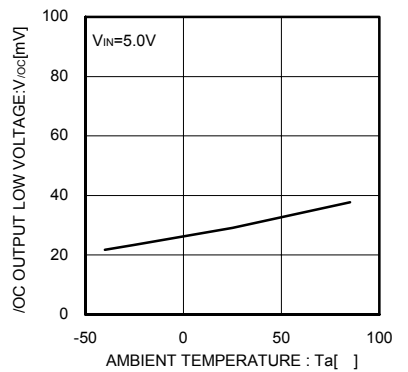


Fig.15 /OC output low voltage

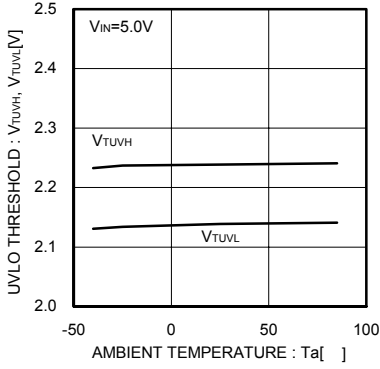


Fig.16 UVLO threshold

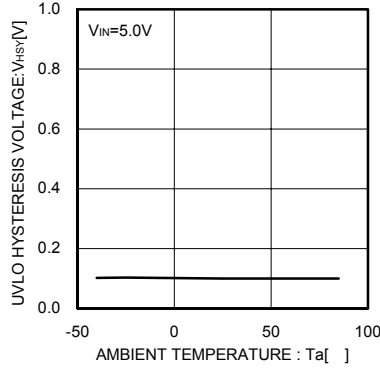


Fig.17 UVLO hysteresis voltage

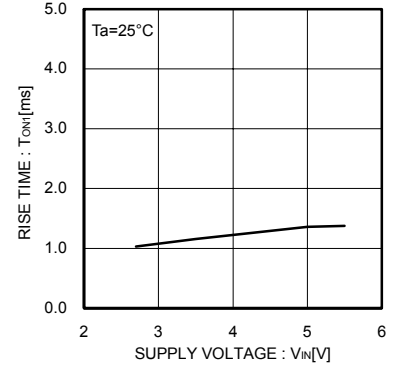


Fig.18 Output rise time

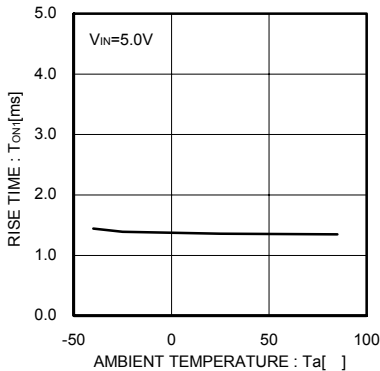


Fig.19 Output rise time

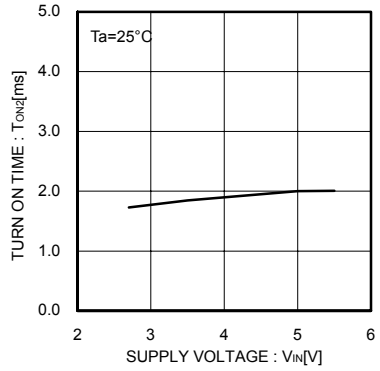


Fig.20 Output turn-on time

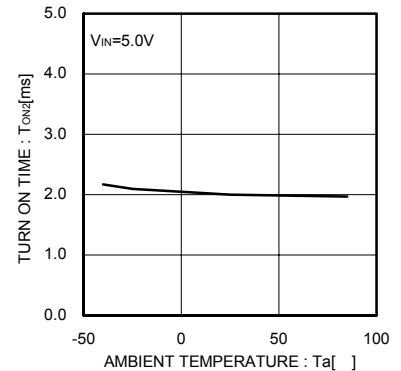


Fig.21 Output turn-on time

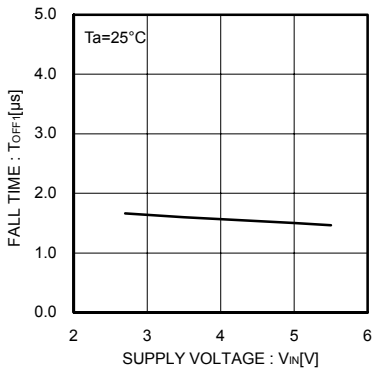


Fig.22 Output fall time

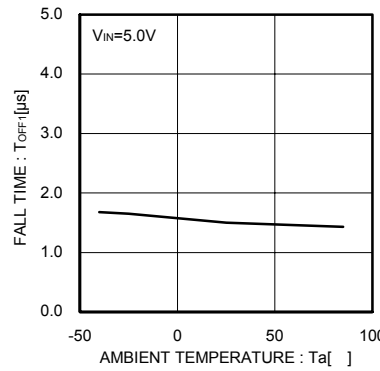


Fig.23 Output fall time

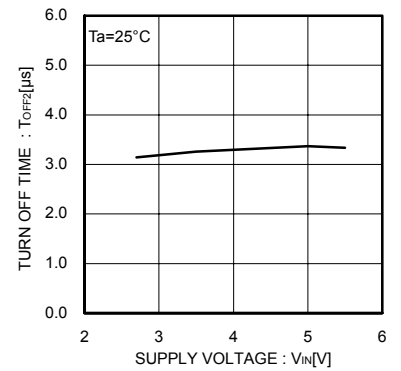


Fig.24 Output turn-off time

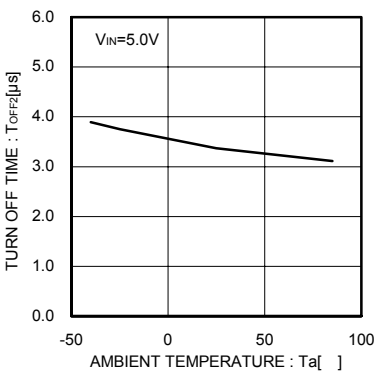


Fig.25 Output turn-off time

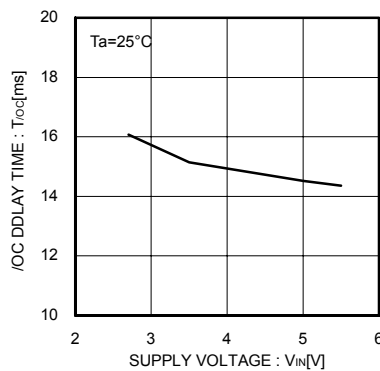


Fig.26 /OC delay time

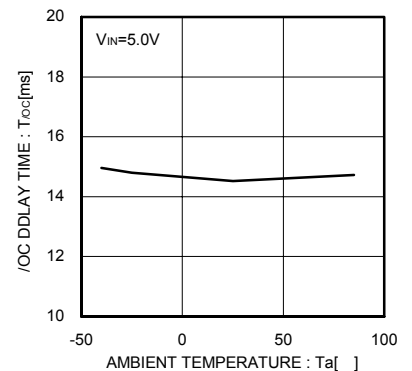


Fig.27 /OC delay time

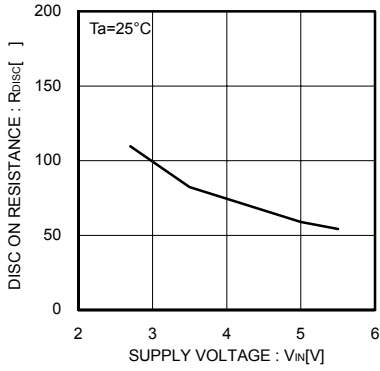


Fig.28 Discharge on resistance

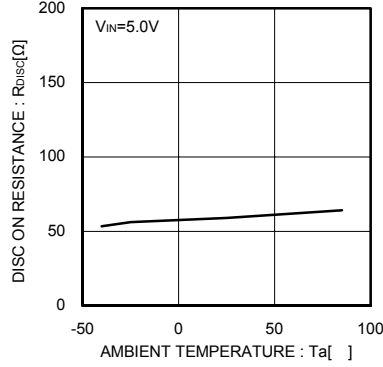


Fig.29 Discharge on resistance

Waveform Data (BD2246G)

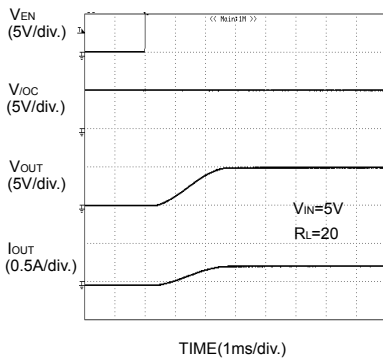


Fig.30 Output rise characteristic

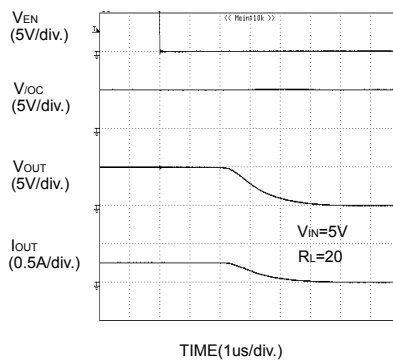


Fig.31 Output fall characteristic

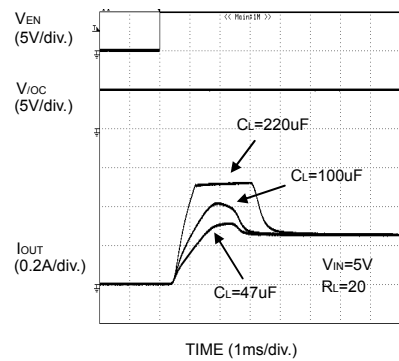


Fig.32 Inrush current response

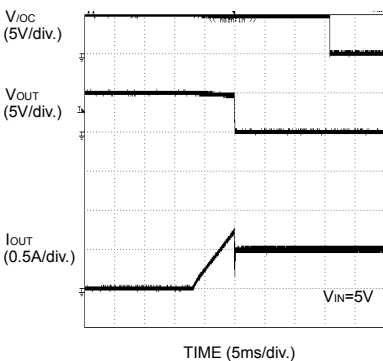


Fig.33 Over-current response ramped load

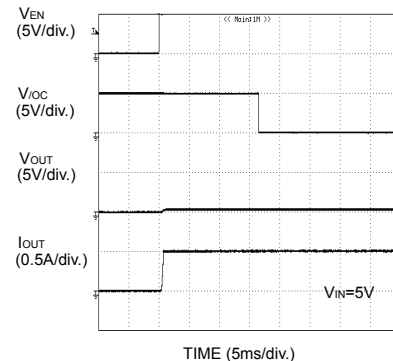


Fig.34 Over-current response enable to shortcircuit

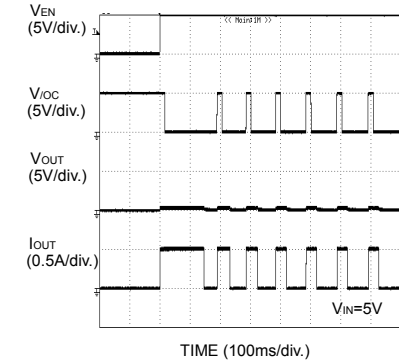


Fig.35 Over-current response enable to shortcircuit

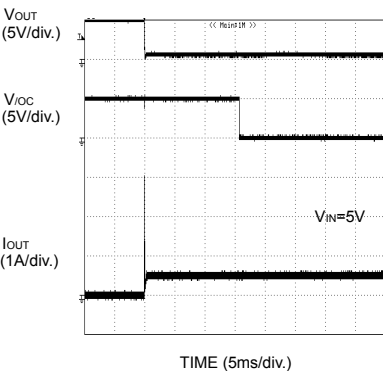


Fig.36 Over-current response 1Ω load to enabled device

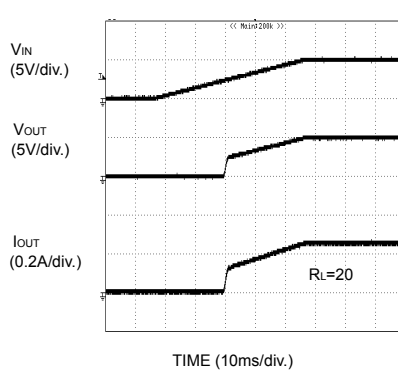


Fig.37 UVLO response increasing Vin

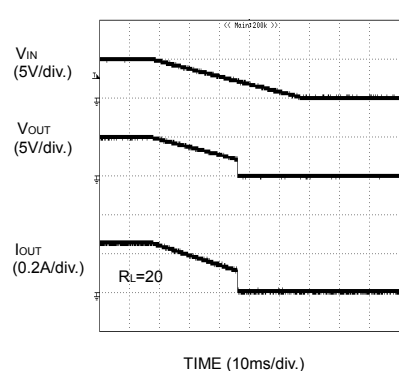


Fig.38 UVLO response decreasing Vin

Block Diagram

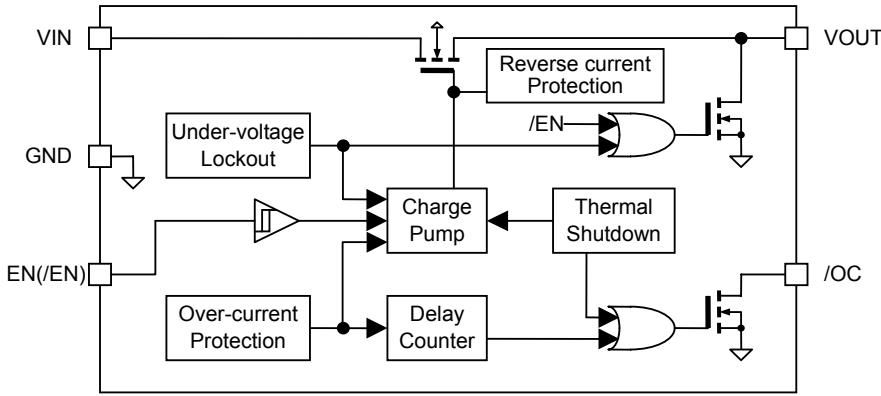


Fig.39 Block diagram

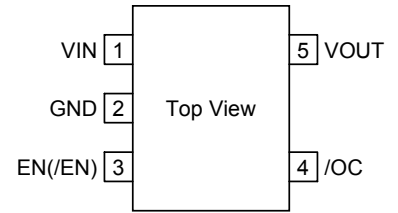


Fig.40 Pin configuration

Pin Description

Pin No.	Symbol	I/O	Function
1	VIN	-	Switch input and the supply voltage for the IC.
2	GND	-	Ground.
3	EN, /EN	I	Enable input. EN: High level input turns on the switch. (BD2246G) /EN: Low level input turns on the switch. (BD2247G)
4	/OC	O	Over-current notification terminal. Low level output during over-current or over-temperature condition. Open-drain fault flag output.
5	VOUT	O	Switch output.

I/O Circuit

Symbol	Pin No.	Equivalent Circuit
EN (/EN)	3	
VOUT	5	
/OC	4	

Functional Description

1. Switch Operation

VIN terminal and VOUT terminal are connected to the drain and the source of switch MOSFET respectively. And the VIN terminal is used also as power source input to internal control circuit.

When the switch is turned on from EN,/EN control input, VIN terminal and VOUT terminal are connected by a 110mΩ(Typ.) switch. In on status, the switch is bidirectional. Therefore, when the potential of VOUT terminal is higher than that of VIN terminal, current flows from VOUT terminal to VIN terminal.

Since a parasitic diode between the drain and the source of switch MOSFET is canceled, in the off status, it is possible to prevent current from flowing reversely from VOUT to VIN.

2. Thermal Shutdown Circuit (TSD)

If over-current would continue, the temperature of the IC would increase drastically. If the junction temperature were beyond 135 (Typ.) in the condition of over-current detection, thermal shutdown circuit operates and makes power switch turn off and outputs fault flag (/OC). Then, when the junction temperature decreases lower than 115 (Typ.), power switch is turned on and fault flag (/OC) is cancelled. Unless the fact of the increasing chips temperature is removed or the output of power switch is turned off, this operation repeats.

The thermal shutdown circuit operates when the switch is on (EN,/EN signal is active).

3. Over-Current Detection (OCD)

The over-current detection circuit limits current (I_{SC}) and outputs fault flag (/OC) when current flowing in each switch MOSFET exceeds a specified value. There are three types of response against over-current. The over-current detection circuit works when the switch is on (EN,/EN signal is active).

3-1. When the switch is turned on while the output is in shortcircuit status

When the switch is turned on while the output is in shortcircuit status or so, the switch gets in current limit status soon.

3-2. When the output shortcircuits while the switch is on

When the output shortcircuits or large capacity is connected while the switch is on, very large current flows until the over-current limit circuit reacts. When the current detection, limit circuit works, current limitation is carried out.

3-3. When the output current increases gradually

When the output current increases gradually, current limitation does not work until the output current exceeds the over-current detection value. When it exceeds the detection value, current limitation is carried out.

4. Under-Voltage Lockout (UVLO)

UVLO circuit prevents the switch from turning on until the VIN exceeds 2.3V(Typ.). If the VIN drops below 2.2V(Typ.) while the switch turns on, then UVLO shuts off the power switch. UVLO has hysteresis of a 100mV(Typ.).

Under-voltage lockout circuit works when the switch is on (EN,/EN signal is active).

5. Fault Flag (/OC) Output

Fault flag output is N-MOS open drain output. At detection of over-current, thermal shutdown, low level is output.

Over-current detection has delay filter. This delay filter prevents instantaneous current detection such as inrush current at switch on, hot plug from being informed to outside.

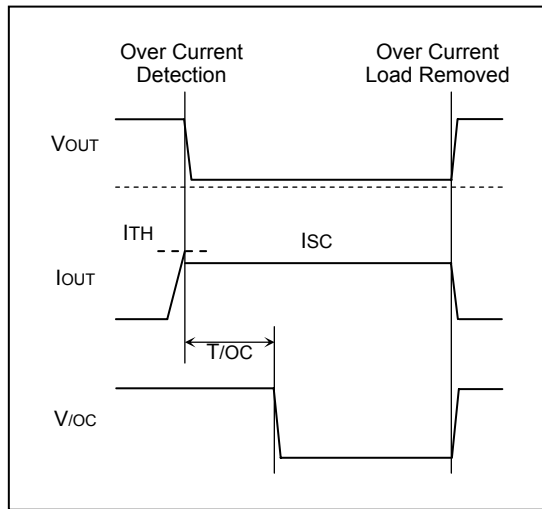


Fig.41 Over-current detection

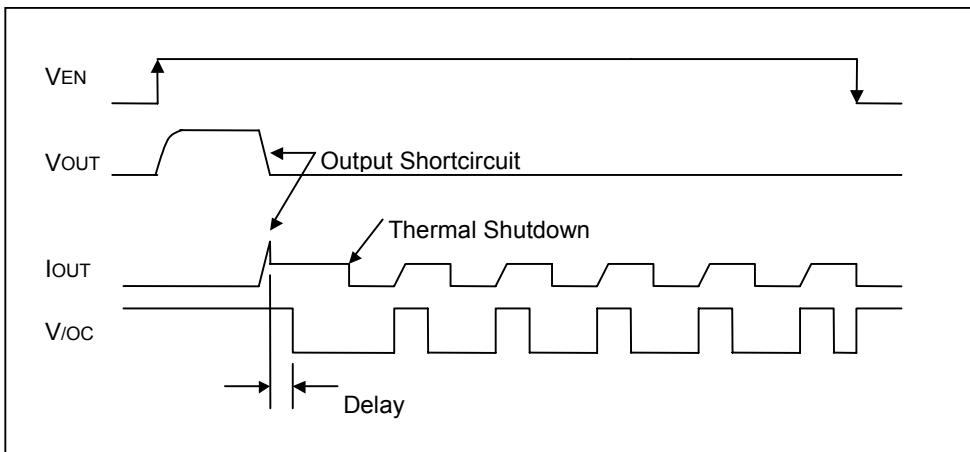


Fig.42 Over-current detection, Thermal shutdown timing (BD2246G)

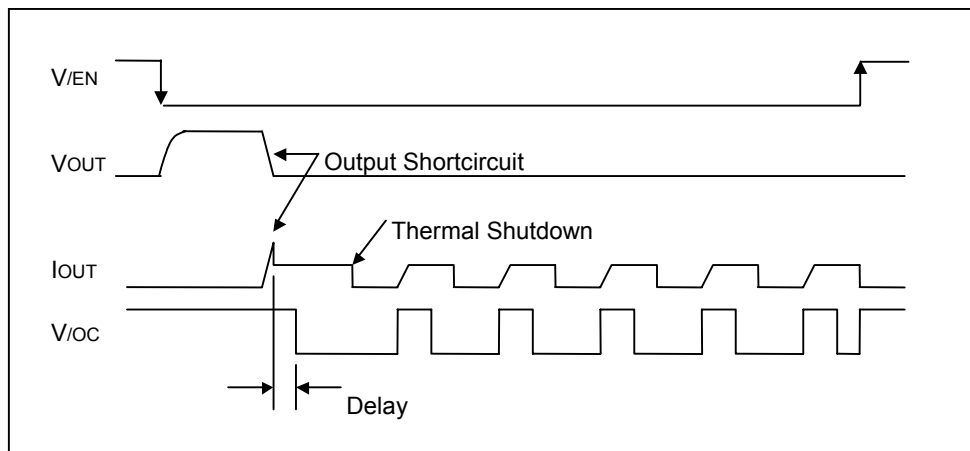


Fig.43 Over-current detection, Thermal shutdown timing (BD2247G)

Typical Application Circuit

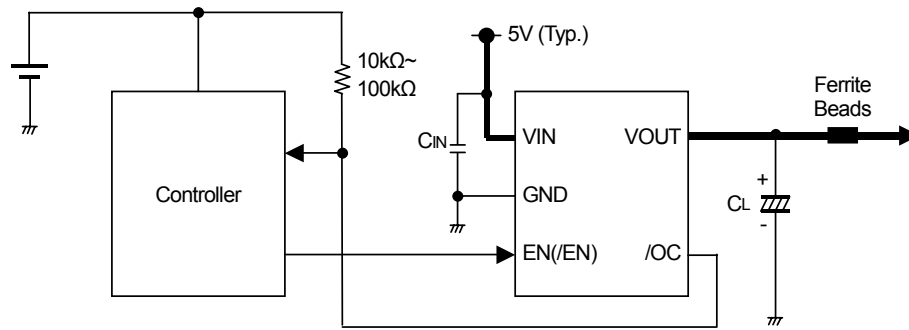


Fig.44 Typical application circuit

Application Information

When excessive current flows owing to output shortcircuit or so, ringing occurs by inductance of power source line to IC, and may cause bad influences upon IC actions. In order to avoid this case, connect a bypass capacitor C_{IN} by VIN terminal and GND terminal of IC. 1 μ F or higher is recommended. In order to decrease voltage fluctuations of power source line to IC, connect a low ESR capacitor in parallel with C_{IN} . 10 μ F ~ 100 μ F or higher is effective.

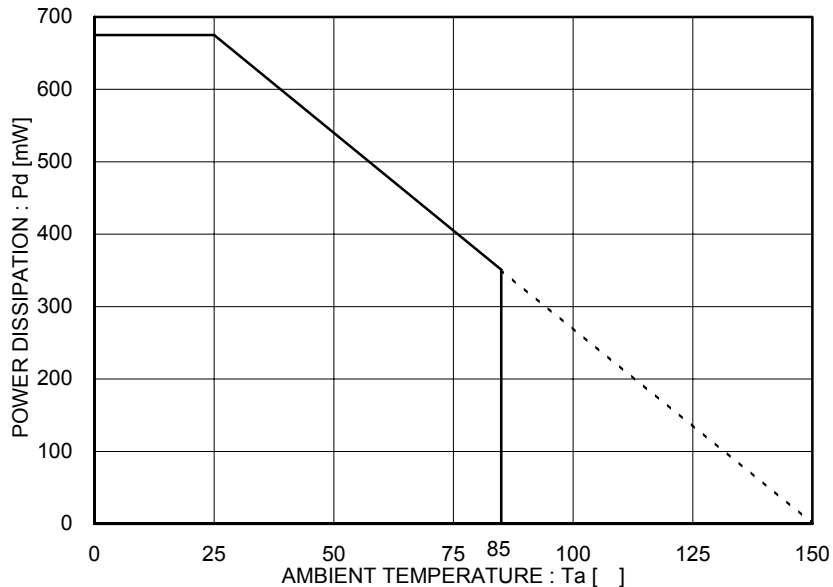
Pull up /OC output by resistance 10k Ω ~ 100k Ω .

Set up value which satisfies the application as C_L and Ferrite Beads.

This system connection diagram doesn't guarantee operating as the application.

When using the circuit with changes to the external circuit constants, make sure to leave an adequate margin for external components including static and transitional characteristics as well as dispersion of the IC.

Power Dissipation Characteristic
(SSOP5 package)



* 70mm x 70mm x 1.6mm Glass Epoxy Board

Fig.45 Power Dissipation Curve (Pd-Ta Curve)

Notes for use

- (1) Absolute maximum ratings
An excess in the absolute maximum ratings, such as supply voltage, temperature range of operating conditions, etc., can break down devices, thus making impossible to identify breaking mode such as a short circuit or an open circuit. If any special mode exceeding the absolute maximum ratings is assumed, consideration should be given to take physical safety measures including the use of fuses, etc.
- (2) Operating conditions
These conditions represent a range within which characteristics can be provided approximately as expected. The electrical characteristics are guaranteed under the conditions of each parameter.
- (3) Reverse connection of power supply connector
The reverse connection of power supply connector can break down ICs. Take protective measures against the breakdown due to the reverse connection, such as mounting an external diode between the power supply and the IC's power supply terminal.
- (4) Power supply line
Design PCB pattern to provide low impedance for the wiring between the power supply and the GND lines. In this regard, for the digital block power supply and the analog block power supply, even though these power supplies has the same level of potential, separate the power supply pattern for the digital block from that for the analog block, thus suppressing the diffraction of digital noises to the analog block power supply resulting from impedance common to the wiring patterns. For the GND line, give consideration to design the patterns in a similar manner. Furthermore, for all power supply terminals to ICs, mount a capacitor between the power supply and the GND terminal. At the same time, in order to use an electrolytic capacitor, thoroughly check to be sure the characteristics of the capacitor to be used present no problem including the occurrence of capacity dropout at a low temperature, thus determining the constant.
- (5) GND voltage
Make setting of the potential of the GND terminal so that it will be maintained at the minimum in any operating state. Furthermore, check to be sure no terminals are at a potential lower than the GND voltage including an actual electric transient.
- (6) Short circuit between terminals and erroneous mounting
In order to mount ICs on a set PCB, pay thorough attention to the direction and offset of the ICs. Erroneous mounting can break down the ICs. Furthermore, if a short circuit occurs due to foreign matters entering between terminals or between the terminal and the power supply or the GND terminal, the ICs can break down.
- (7) Operation in strong electromagnetic field
Be noted that using ICs in the strong electromagnetic field can malfunction them.
- (8) Inspection with set PCB
On the inspection with the set PCB, if a capacitor is connected to a low-impedance IC terminal, the IC can suffer stress. Therefore, be sure to discharge from the set PCB by each process. Furthermore, in order to mount or dismount the set PCB to/from the jig for the inspection process, be sure to turn OFF the power supply and then mount the set PCB to the jig. After the completion of the inspection, be sure to turn OFF the power supply and then dismount it from the jig. In addition, for protection against static electricity, establish a ground for the assembly process and pay thorough attention to the transportation and the storage of the set PCB.
- (9) Input terminals
In terms of the construction of IC, parasitic elements are inevitably formed in relation to potential. The operation of the parasitic element can cause interference with circuit operation, thus resulting in a malfunction and then breakdown of the input terminal. Therefore, pay thorough attention not to handle the input terminals, such as to apply to the input terminals a voltage lower than the GND respectively, so that any parasitic element will operate. Furthermore, do not apply a voltage to the input terminals when no power supply voltage is applied to the IC. In addition, even if the power supply voltage is applied, apply to the input terminals a voltage lower than the power supply voltage or within the guaranteed value of electrical characteristics.
- (10) Ground wiring pattern
If small-signal GND and large-current GND are provided, It will be recommended to separate the large-current GND pattern from the small-signal GND pattern and establish a single ground at the reference point of the set PCB so that resistance to the wiring pattern and voltage fluctuations due to a large current will cause no fluctuations in voltages of the small-signal GND. Pay attention not to cause fluctuations in the GND wiring pattern of external parts as well.
- (11) External capacitor
In order to use a ceramic capacitor as the external capacitor, determine the constant with consideration given to a degradation in the nominal capacitance due to DC bias and changes in the capacitance due to temperature, etc.
- (12) Thermal shutdown circuit (TSD)
When junction temperatures become detected temperatures or higher, the thermal shutdown circuit operates and turns a switch OFF. The thermal shutdown circuit is aimed at isolating the LSI from thermal runaway as much as possible. Do not continuously use the LSI with this circuit operating or use the LSI assuming its operation.
- (13) Thermal design
Perform thermal design in which there are adequate margins by taking into account the power dissipation (Pd) in actual states of use.

Ordering part number

B	D
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Part No.

2	2	4	6
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Part No.
2246
2247

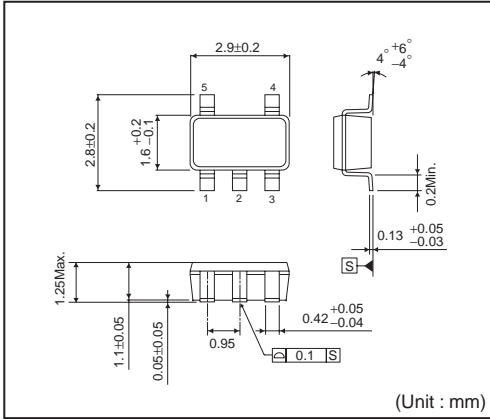
G

Package
G: SSOP5

T	R
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Packaging and forming specification
TR: Embossed tape and reel

SSOP5



<Tape and Reel information>

Tape	Embossed carrier tape
Quantity	3000pcs
Direction of feed	TR (The direction is the 1pin of product is at the upper right when you hold reel on the left hand and you pull out the tape on the right hand)

